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April 2013

FQP47P06

P-Channel QFET® MOSFET

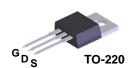
- 60 V, - 47 A, 26 mΩ

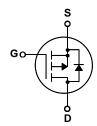
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconducto®'s proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 47 A, 60 V, $R_{DS(on)}$ = 26 m Ω @ V_{GS} = 10 V, I_D = 23.5 A
- Low Gate Charge (Typ. 84 nC)
- Low Crss (yp. 320 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temrature Rating.





Absolute Maximum Ratings $T_C = 25$ °C unless otherwise noted

Symbol	Parameter		FQP47P06	Unit
V _{DSS}	Drain-Source Voltage		-60	V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		-47	А
			-33.2	А
I _{DM}	Drain Current - Pulsed	(Note 1)	-188	А
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	820	mJ
I _{AR}	Avalanche Current	(Note 1)	-47	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	16	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-7.0	V/ns
P_D	Power Dissipation (T _C = 25°C)		160	W
	- Derate above 25°C		1.06	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQP47P06	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.94	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-0.06		V/°(
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -60 V, V _{GS} = 0 V			-1	μΑ
		V _{DS} = -48 V, T _C = 150°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -25 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 25 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -23.5 A		0.021	0.026	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = -30 \text{ V}, I_D = -23.5 \text{ A}$ (Note 4)		21		S
C _{iss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = -25 \text{ V, } V_{GS} = 0 \text{ V,}$ f = 1.0 MHz		2800 1300	3600 1700	pF pF
C _{rss}	Reverse Transfer Capacitance			320	420	pF
Switchi	ing Characteristics		1	1	1	ı
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -30 \text{ V}, I_D = -23.5 \text{ A},$		50	110	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		450	910	ns
t _{d(off)}	Turn-Off Delay Time			100	210	ns
t _f	Turn-Off Fall Time	(Note 4, 5)		195	400	ns
Q_g	Total Gate Charge	$V_{DS} = -48 \text{ V}, I_{D} = -47 \text{ A},$		84	110	nC
Q_{gs}	Gate-Source Charge	V _{GS} = -10 V		18		nC
Q_{gd}	Gate-Drain Charge	(Note 4, 5)		44		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				-47	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F				-188	Α
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = -47 \text{ A}$			-4.0	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{S} = -47 \text{ A},$		130		ns
Q _{rr}	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$ (Note 4)		0.55	1	μC

- **Notes:**1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 0.43mH, I_{AS} = -47A, V_{DD} = -25V, R_G = 25 Ω , Starting T_J = 25°C 3. I_{SD} \leq -47A, di/dt \leq 300A/µs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C 4. Pulse Test : Pulse width \leq 300µs, Duty cycle \leq 2% 5. Essentially independent of operating temperature

Typical Characteristics

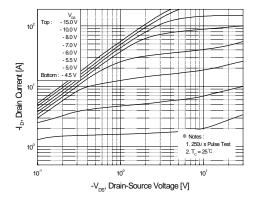


Figure 1. On-Region Characteristics

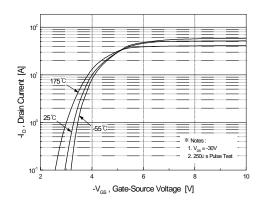


Figure 2. Transfer Characteristics

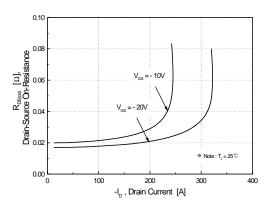


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

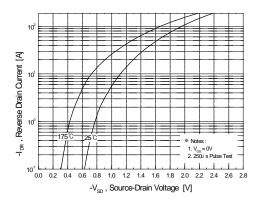


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

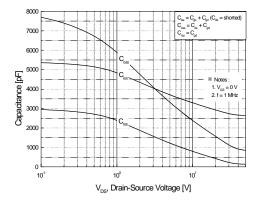


Figure 5. Capacitance Characteristics

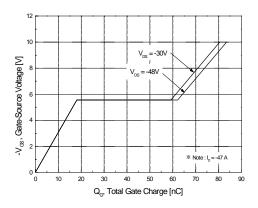


Figure 6. Gate Charge Characteristics

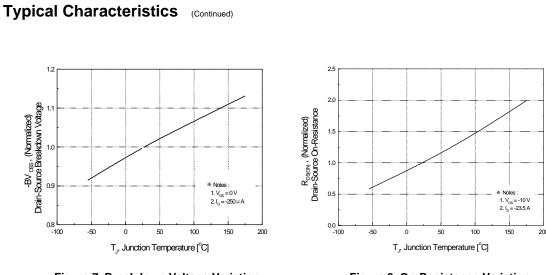


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature

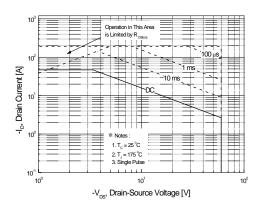


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

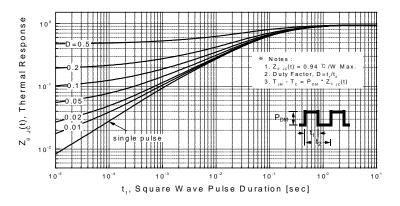
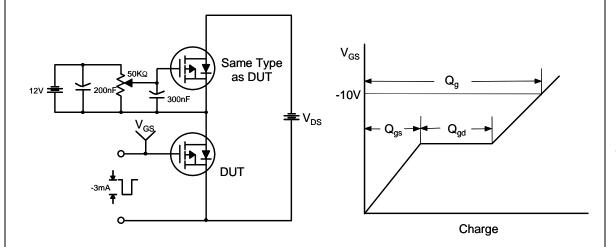
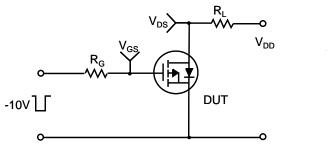


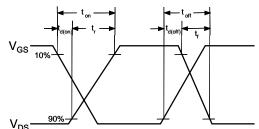
Figure 11. Transient Thermal Response Curve

Gate Charge Test Circuit & Waveform

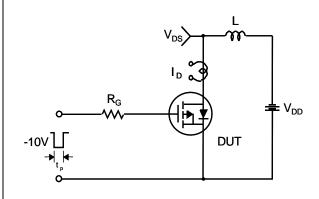


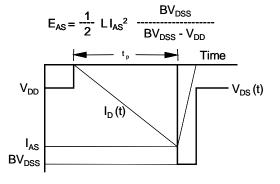
Resistive Switching Test Circuit & Waveforms



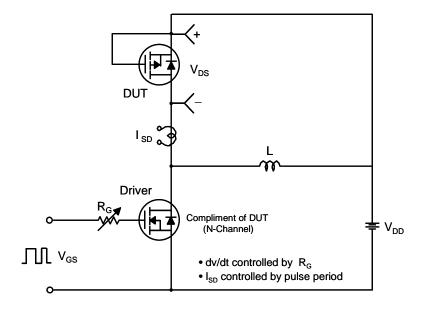


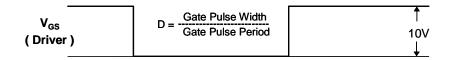
Unclamped Inductive Switching Test Circuit & Waveforms

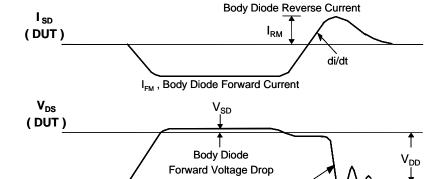




Peak Diode Recovery dv/dt Test Circuit & Waveforms



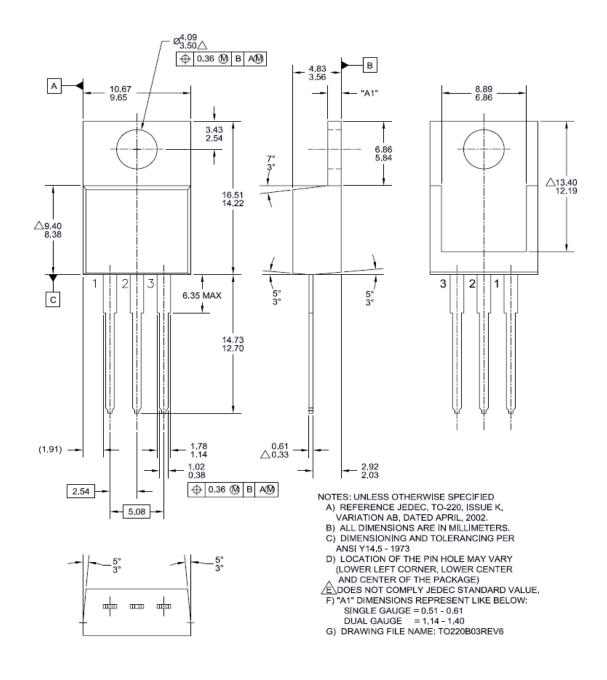




Body Diode Recovery dv/dt

Mechanical Dimensions

TO-220B03



Dimensions in Millimeters





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